

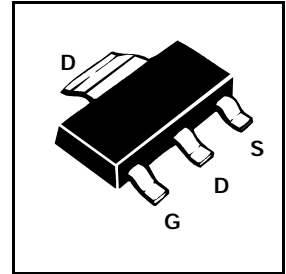
SOT223 N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ZVN4206G

ISSUE 3 - JANUARY 1996

FEATURES

- * Compact geometry
- * Fast switching speeds
- * No secondary breakdown and Excellent temperature stability
- * High input impedance and low current drive
- * Ease of paralleling



APPLICATIONS

- * DC-DC converters
- * Solenoid / relay drivers for automotive applications
- * Stepper motor drivers and Print head drivers

PARTMARKING DETAIL - ZVN4206

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	1	A
Pulsed Drain Current	I_{DM}	8	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ZVN4206G

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

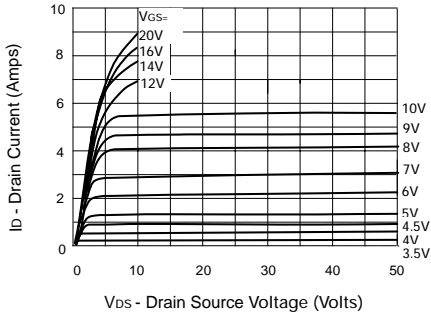
PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	V_{DSS}	60		V	$I_D=1\text{mA}, V_{GS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	1.3	3	V	$I_D=1\text{mA}, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		100	nA	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}		10 100	μA μA	$V_{DS}=60\text{V}, V_{GS}=0\text{V}$ $V_{DS}=48\text{V}, V_{GS}=0\text{V}, T=125^{\circ}\text{C}(2)$
On-State Drain Current (1)	$I_{D(on)}$	3		A	$V_{DS}=25\text{V}, V_{GS}=10\text{V}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		1 1.5	Ω Ω	$V_{GS}=10\text{V}, I_D=1.5\text{A}$ $V_{GS}=5\text{V}, I_D=0.5\text{A}$
Forward Transconductance (1)(2)	g_{fs}	300		mS	$V_{DS}=25\text{V}, I_D=1.5\text{A}$
Input Capacitance (2)	C_{iss}		100	pF	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$
Common Source Output Capacitance (2)	C_{oss}		60	pF	
Reverse Transfer Capacitance (2)	C_{rss}		20	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		8	ns	$V_{DD}\approx 25\text{V}, I_D=1.5\text{A}, V_{GEN}=10\text{V}$
Rise Time (2)(3)	t_r		12	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		12	ns	
Fall Time (2)(3)	t_f		15	ns	

(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$

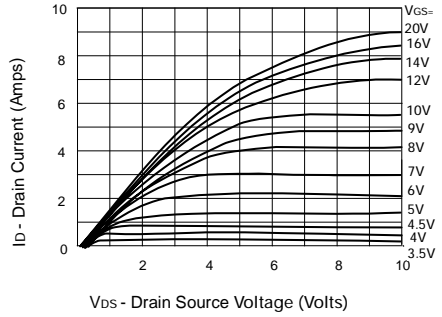
(2) Sample test.

(3) Switching times measured with 50 Ω source impedance and <5ns rise time on a pulse generator

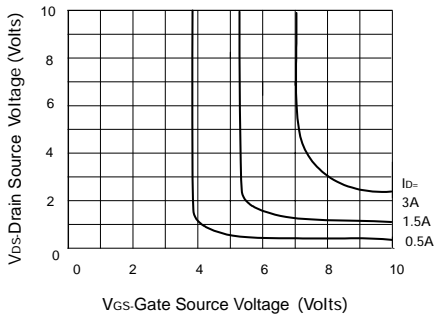
TYPICAL CHARACTERISTICS



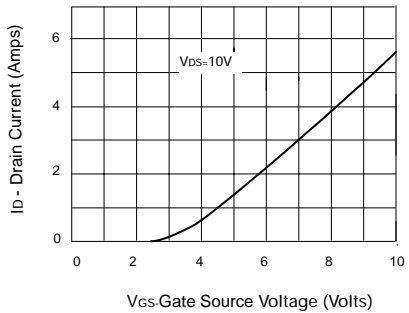
Output Characteristics



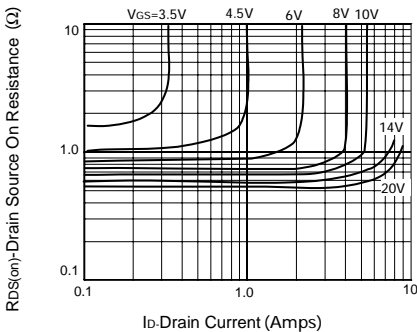
Saturation Characteristics



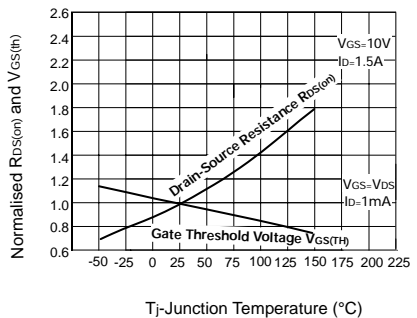
Voltage Saturation Characteristics



Transfer Characteristics



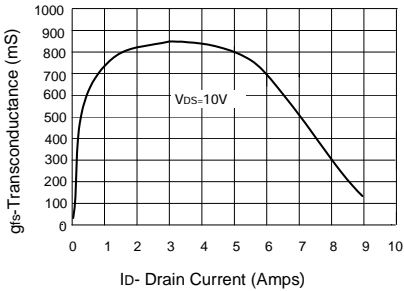
On-resistance v drain current



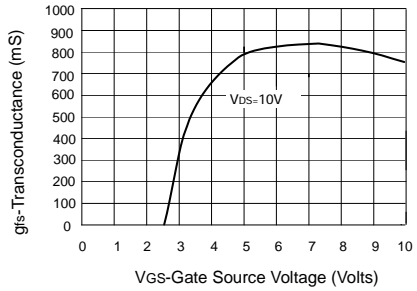
Normalised $R_{DS(on)}$ and $V_{GS(th)}$ v Temperature

ZVN4206G

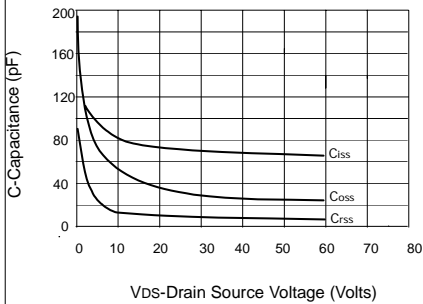
TYPICAL CHARACTERISTICS



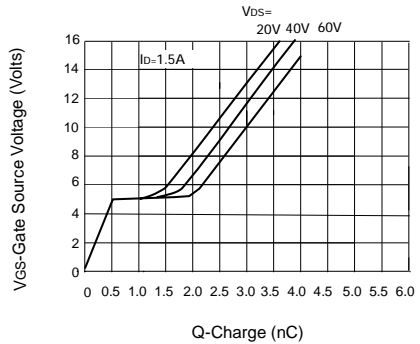
Transconductance v drain current



Transconductance v gate-source voltage



Capacitance v drain-source voltage



Gate charge v gate-source voltage